Freescale Semiconductor

Technical Data

Document Number: MMG2401 Rev. 3, 5/2006

MMG2401NR2

2400-2500 MHz, 27.5 dB, 26.5 dBm

802.11g WLAN POWER AMPLIFIER InGaP HBT

VRoHS

Indium Gallium Phosphorus HBT WLAN Power Amplifier

Designed for 802.11g and dual mode applications with frequencies from 2400 to 2500 MHz.

- 26.5 dBm P1dB @ 2450 MHz
- Power Gain: 27.5 dB Typ (@ f = 2450 MHz, Class AB)
- High Gain, High Efficiency and High Linearity
- EVM = 3% Typ @ P_{out} = +19 dBM, 14% PAE
- RoHS Compliant
- In Tape and Reel. R2 Suffix = 1,500 Units per 12 mm, 7 inch Reel.



Table 1. Maximum Ratings

| Rating | Symbol | Value | Unit |
|--------------------------|-------------------|-------|------|
| Collector Supply | V _{CC} | 5 | V |
| Base Supply First Stage | V _{B1} | 5 | V |
| Base Supply Second Stage | V _{B2} | 5 | V |
| Detector Bias Supply | V _{BIAS} | 5 | V |
| DC Current | I _{DC} | 171 | mA |

Table 2. Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--------------------------------------|------------------|--------------|------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 185 (1) | °C/W |
| Case Operating Temperature Range | T _C | - 40 to +85 | °C |
| Storage Temperature Range | T _{stg} | - 55 to +150 | °C |

Table 3. ESD Protection Characteristics

| Test Methodology | Class |
|---------------------------------------|--------------|
| Human Body Model (per JESD22-A114) | 2 (Minimum) |
| Machine Model (per EIA/JESD22-A115) | A (Minimum) |
| Charge Device Model (per JESD22-C101) | II (Minimum) |

Table 4. Moisture Sensitivity Level

| Test Methodology | Rating | Package Peak Temperature | Unit |
|---------------------------------------|--------|--------------------------|------|
| Per JESD 22-A113, IPC/JEDEC J-STD-020 | 1 | 260 | °C |

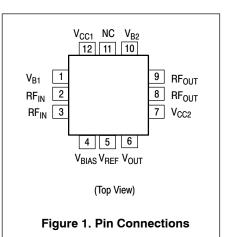
1. Simulated.

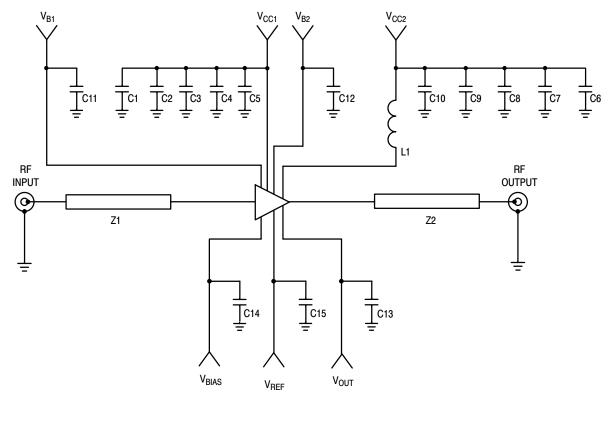


| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|---------------------|-----|------|------|------|
| Output Power at 1dB Compression | P1dB | 24 | 26.5 | _ | dBm |
| Power Gain (P _{out} = 19 dBm) | G _p | 26 | 27.5 | 29 | dB |
| Error Vector Magnitude (P _{out} = 19 dBm, 64 QAM/54 Mbps) | EVM | | 3 | _ | % |
| Total Current (P _{out} = 19 dBm) | I _{Ctotal} | | 210 | _ | mA |
| Quiescent Current | IDCQ | _ | 156 | _ | mA |
| Bias Control Reference Current (I _{CQ} = 66 mA) | I _{ref} | | 8.4 | _ | mA |
| Gain Flatness (Over 100 MHz) | G _F | | ±0.2 | _ | dB |
| Gain Variation over Temperature (-40 to 85°C) | - | | ±1 | _ | dB |
| Input Return Loss | IRL | _ | - 10 | -7.5 | dB |
| Reverse Isolation | — | _ | -35 | _ | dB |
| Second Harmonic (P _{out} = 19 dBm) | - | | -45 | _ | dBc |
| Third Harmonic (P _{out} = 19 dBm) | - | | -35 | _ | dBc |
| Ramp-On Time (10-90%) | t _{ON} | _ | 100 | _ | ns |

Table 5. Electrical Characteristics (T_A = 25°C unless otherwise noted.) V_{CC} = 3.3 Vdc, V_{BIAS} = 3 Vdc, I_{CQ} = 83 mA, f = 2450 MHz

| Name | Pin Number | Description | | |
|-------------------|-----------------------------|---|--|--|
| V _{B1} | 1 | Base power supply for first stage amplifier. | | |
| RF _{IN} | 2, 3 | RF input for the power amplifier. This pin is DC-shorted to GND and AC-coupled to the transistor base of the first stage. | | |
| V _{BIAS} | 4 | Detector bias voltage supply. | | |
| V _{REF} | 5 | Detector output voltage reference. V _{out} - V _{REF} is useful for tracking detector performance over temperature. | | |
| V _{OUT} | 6 | Detector output voltage. | | |
| V _{CC2} | 7 | Collector power supply for second stage amplifier. | | |
| RF _{OUT} | 8, 9 | RF output for the power amplifier. This pin is DC-coupled and requires a DC-blocking series capacitor. | | |
| V _{B2} | 10 | Base power supply for second stage amplifier. | | |
| NC | 11 | Not connected. | | |
| V _{CC1} | 12 | Collector power supply for first stage amplifier. | | |
| GND | Backside Center Metal | The center metal base of the QFN 3x3 package provides both DC and RF ground as well as heat sink contact for the power amplifier. | | |

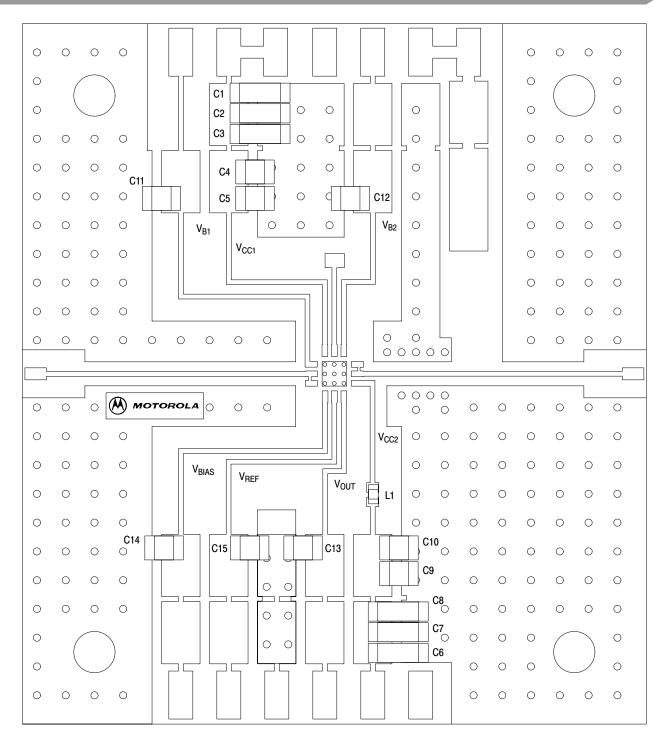




| Z1, Z2 | 0.10" x 0.5395" Microstrip |
|--------|--|
| PCB | Getek ML200M, 0.005", $\epsilon_r = 3.8$ |



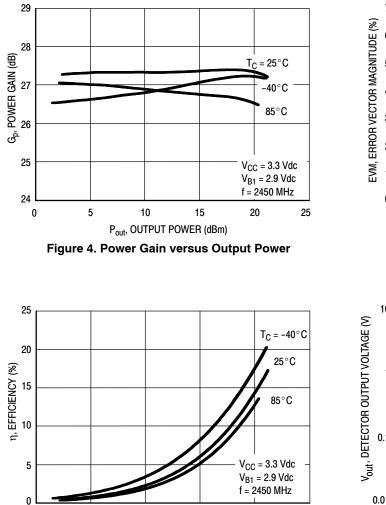
| Part | Description | Part Number | Manufacturer |
|------------------------|------------------------|----------------|--------------|
| C1, C6 | 1 μF Chip Capacitor | 12065A105JAT2A | AVX |
| C2, C7 | 0.1 µF Chip Capacitor | 12065A104JAT2A | AVX |
| C3, C8 | 0.01 µF Chip Capacitor | 12065A103JAT2A | AVX |
| C4, C9, C11, C12 | 100 pF Chip Capacitor | 08055A101FAT2A | AVX |
| C5, C10, C13, C14, C15 | 20 pF Chip Capacitor | 12065A200CAT2A | AVX |
| L1 | 7.5 nH Chip Inductor | 0402CS-7N5XJBC | Coilcraft |



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Figure 3. MMG2401NR2 Test Circuit Component Layout

TYPICAL CHARACTERISTICS



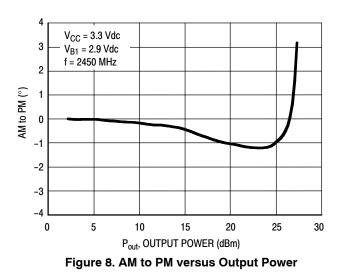
P_{out}, OUTPUT POWER (dBm) Figure 6. Efficiency versus Output Power

15

20

25

10





0

5

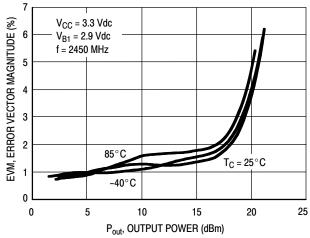


Figure 5. Error Vector Magnitude versus Output Power

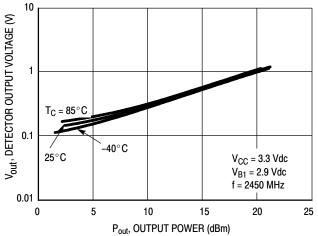


Figure 7. Detector Output Voltage versus Output Power

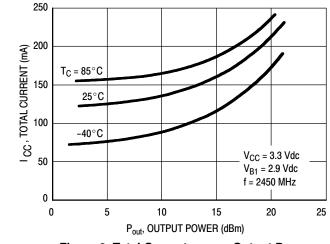
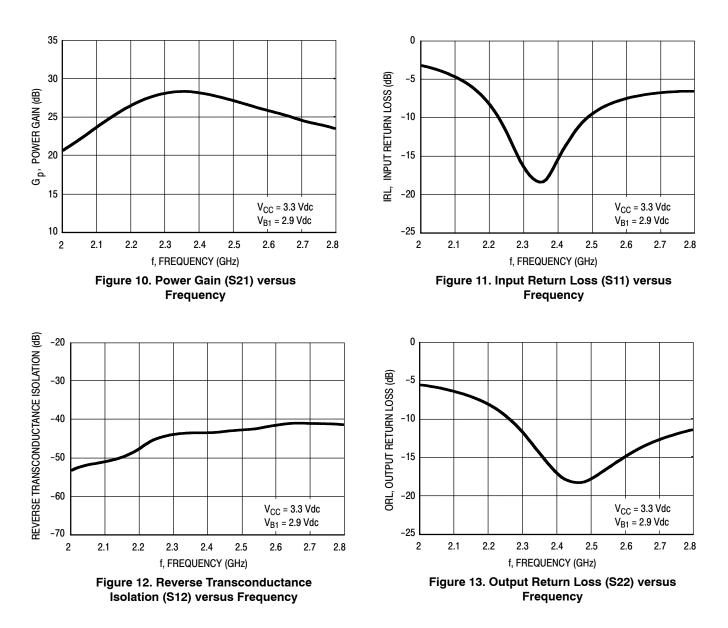


Figure 9. Total Current versus Output Power

TYPICAL CHARACTERISTICS



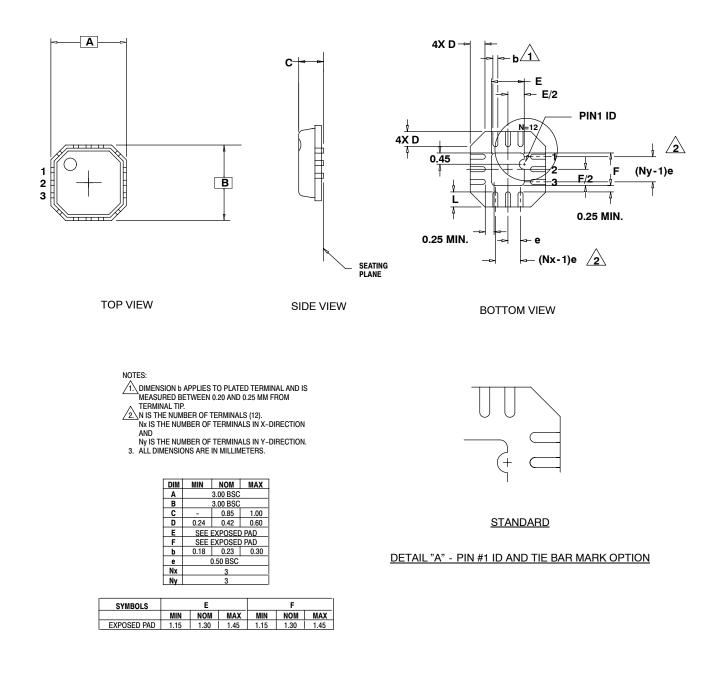
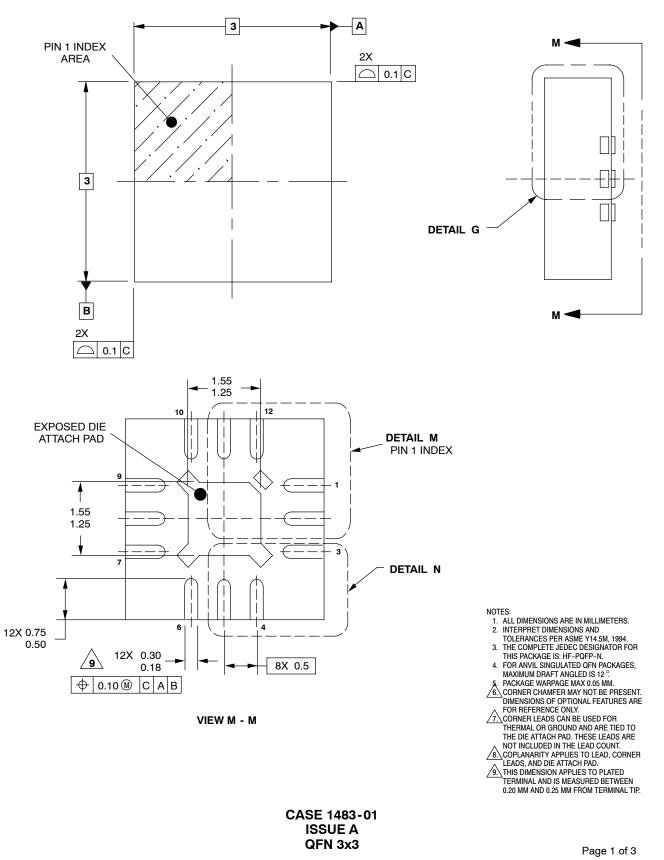
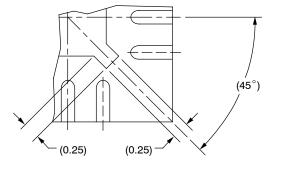


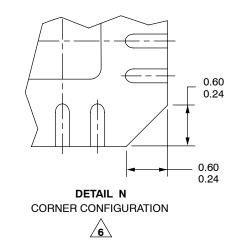
Figure 14. MMG2401NR2 Specific Mechanical Outline Information

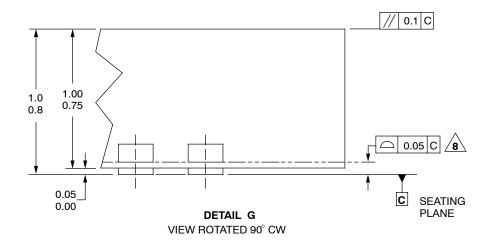
PACKAGE DIMENSIONS





DETAIL N PREFERRED CORNER CONFIGURATION



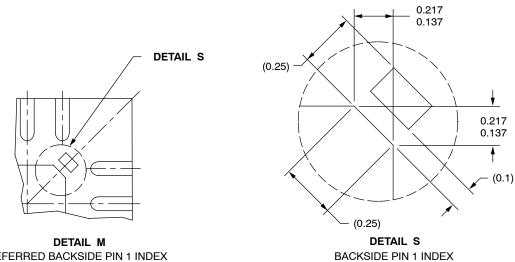


CASE 1483-01 ISSUE A QFN 3x3

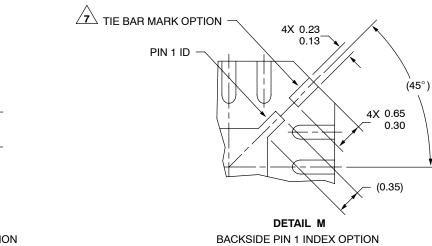
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RF Device Data Freescale Semiconductor

MMG2401NR2







(0.45) R0.2 -PIN 1 ID DETAIL M BACKSIDE PIN 1 INDEX OPTION

> CASE 1483-01 **ISSUE A** QFN 3x3

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